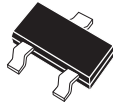


CMPT6517 NPN
CMPT6520 PNP

COMPLEMENTARY SILICON
HIGH VOLTAGE TRANSISTORS



SOT-23 CASE

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT6517, CMPT6520 types are complementary silicon transistors manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for high voltage driver and amplifier applications.

MARKING CODE:

CMPT6517: C1Z

CMPT6520: C2Z

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

| | SYMBOL | | UNITS |
|------------------------------|----------------|-------------|--------------------|
| Collector-Base Voltage | V_{CBO} | 350 | V |
| Collector-Emitter Voltage | V_{CEO} | 350 | V |
| Emitter-Base Voltage | V_{EBO} | 5.0 | V |
| Continuous Collector Current | I_C | 500 | mA |
| Base Current | I_B | 250 | mA |
| Power Dissipation | P_D | 350 | mW |
| Operating and Storage | | | |
| Junction Temperature | T_J, T_{stg} | -65 to +150 | $^\circ\text{C}$ |
| Thermal Resistance | θ_{JA} | 357 | $^\circ\text{C/W}$ |

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

| SYMBOL | TEST CONDITIONS | MIN | MAX | UNITS |
|---------------|---------------------------------------|-----|------|-------|
| I_{CBO} | $V_{CB}=250\text{V}$ | | 50 | nA |
| I_{EBO} | $V_{EB}=5.0\text{V}$ (CMPT6517) | | 50 | nA |
| I_{EBO} | $V_{EB}=4.0\text{V}$ (CMPT6520) | | 50 | nA |
| BV_{CBO} | $I_C=100\mu\text{A}$ | 350 | | V |
| BV_{CEO} | $I_C=1.0\text{mA}$ | 350 | | V |
| BV_{EBO} | $I_E=10\mu\text{A}$ (CMPT6517) | 6.0 | | V |
| BV_{EBO} | $I_E=10\mu\text{A}$ (CMPT6520) | 5.0 | | V |
| $V_{CE(SAT)}$ | $I_C=10\text{mA}, I_B=1.0\text{mA}$ | | 0.30 | V |
| $V_{CE(SAT)}$ | $I_C=20\text{mA}, I_B=2.0\text{mA}$ | | 0.35 | V |
| $V_{CE(SAT)}$ | $I_C=30\text{mA}, I_B=3.0\text{mA}$ | | 0.50 | V |
| $V_{CE(SAT)}$ | $I_C=50\text{mA}, I_B=5.0\text{mA}$ | | 1.0 | V |
| $V_{BE(SAT)}$ | $I_C=10\text{mA}, I_B=1.0\text{mA}$ | | 0.75 | V |
| $V_{BE(SAT)}$ | $I_C=20\text{mA}, I_B=2.0\text{mA}$ | | 0.85 | V |
| $V_{BE(SAT)}$ | $I_C=30\text{mA}, I_B=3.0\text{mA}$ | | 0.90 | V |
| $V_{BE(ON)}$ | $I_C=10\text{V}, I_C=100\text{mA}$ | | 2.0 | V |
| h_{FE} | $V_{CE}=10\text{V}, I_C=1.0\text{mA}$ | 20 | | |
| h_{FE} | $V_{CE}=10\text{V}, I_C=10\text{mA}$ | 30 | | |

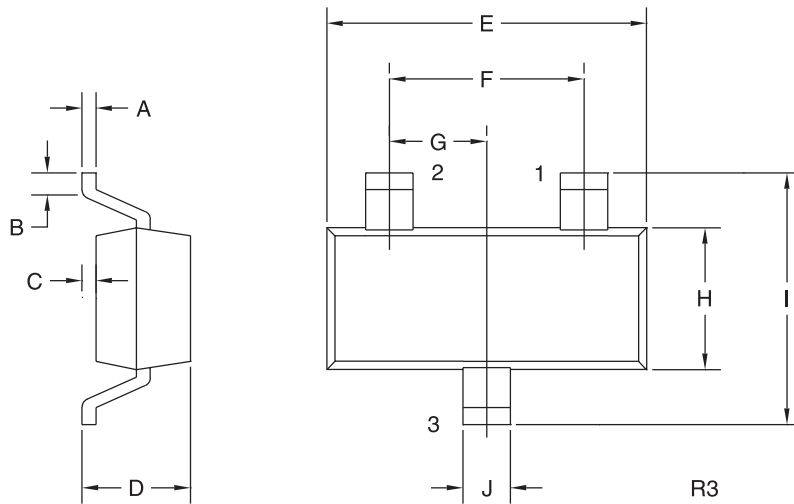
R4 (26-September 2002)

COMPLEMENTARY SILICON HIGH VOLTAGE TRANSISTORS

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

| SYMBOL | TEST CONDITIONS | MIN | MAX | UNITS |
|----------|---|-----|-----|-------|
| h_{FE} | $V_{CE}=10\text{V}, I_C=30\text{mA}$ | 30 | 200 | |
| h_{FE} | $V_{CE}=10\text{V}, I_C=50\text{mA}$ | 20 | 200 | |
| h_{FE} | $V_{CE}=10\text{V}, I_C=100\text{mA}$ | 15 | | |
| f_T | $V_{CE}=20\text{V}, I_C=10\text{mA}, f=20\text{MHz}$ | 40 | 200 | MHz |
| C_{cb} | $V_{CB}=20\text{V}, I_C=0, f=1.0\text{MHz}$ | | 6.0 | pF |
| C_{eb} | $V_{EB}=0.5\text{V}, I_E=0, f=1.0\text{MHz}$ (CMPT6517) | | 80 | pF |
| C_{eb} | $V_{EB}=0.5\text{V}, I_E=0, f=1.0\text{MHz}$ (CMPT6520) | | 100 | pF |

SOT-23 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR

MARKING CODE:

CMPT6517: C1Z
CMPT6520: C2Z

| SYMBOL | DIMENSIONS | | | |
|--------|------------|-------|-------------|------|
| | INCHES | | MILLIMETERS | |
| | MIN | MAX | MIN | MAX |
| A | 0.003 | 0.007 | 0.08 | 0.18 |
| B | 0.006 | - | 0.15 | - |
| C | - | 0.005 | - | 0.13 |
| D | 0.035 | 0.043 | 0.89 | 1.09 |
| E | 0.110 | 0.120 | 2.80 | 3.05 |
| F | 0.075 | | 1.90 | |
| G | 0.037 | | 0.95 | |
| H | 0.047 | 0.055 | 1.19 | 1.40 |
| I | 0.083 | 0.098 | 2.10 | 2.49 |
| J | 0.014 | 0.020 | 0.35 | 0.50 |

SOT-23 (REV: R3)



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